

<<功率半导体器件基础>>

图书基本信息

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内容概要

《功率半导体器件基础（英文版）》作者是功率半导体器件领域的著名专家，IGBT器件发明人之一。
《功率半导体器件基础（英文版）》结合作者多年的实践经验，深入讨论了半导体功率器件的物理模型、工作原理、设计原则和应用特性，不仅详细介绍了硅基器件，还讨论了碳化硅器件的特性与设计要求。

主要内容包括材料特性与输运物理、击穿电压、肖特基整流器、P-i-N整流器、功率MOSFET器件、双极型晶体管、晶闸管、IGBT器件等。

《功率半导体器件基础（英文版）》可作为微电子、电力电子等相关领域科研人员、工程技术人员的参考书，也可作为相关专业高年级本科生、研究生的教材。

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作者简介

无

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